

AMENDMENTS TO THE CLAIMS:

Replacement Claim Set:

1. (Currently amended) An integrated circuit, comprising:
 - a substrate;
 - a porous dielectric layer disposed on the substrate and having a trench disposed therein;
 - a conductor disposed within the trench; and
 - a substantially impermeable barrier pore sealing layer, including at least two different materials bonded together and expanded, located between the conductor and the dielectric layer.
2. (Original) The integrated circuit of Claim 1 wherein one of the materials includes palladium.
3. (Original) The integrated circuit of Claim 1 wherein one of the materials includes platinum.
4. (Currently amended) The integrated circuit of Claim 1 wherein ~~the barrier further one of the materials~~ includes silicon.
5. (Original) The integrated circuit of Claim 1 wherein the conductor includes copper.
6. (Currently amended) The integrated circuit of Claim 1 wherein ~~the barrier pore sealing layer~~ has a thickness between about 2 nm to about 200 nm.
7. (Canceled).
8. (Canceled).
9. (Canceled).
10. (Canceled).
11. (Canceled).

12. (Canceled).
13. (Canceled).
14. (Canceled).
15. (New) The integrated circuit of Claim 1 wherein at least one of the materials includes a dielectric material.
16. (New) The integrated circuit of Claim 1 additionally comprising a barrier material.
17. (New) The integrated circuit of Claim 1 wherein one of the materials is Pt and one of the materials is Si.
18. (New) The integrated circuit of Claim 1 wherein one of the materials is Pd and one of the material is Si.
19. (New) The integrated circuit of Claim 1 wherein the pore sealing layer completely seals the surface pores of the dielectric.
20. (Withdrawn) A method of making the integrated circuit of Claim 1 comprising forming a pore sealing layer on a porous dielectric.
21. (Withdrawn) The method of Claim 20 wherein forming a pore sealing layer comprises depositing a first material.
22. (Withdrawn) The method of Claim 21 wherein forming a pore sealing layer additionally comprises depositing a second material.